

## 1. General description

AC Thyristor Triac power switch in a SOT78 (TO-220AB) plastic package with selfprotective clamping capabilities against low and high energy transients. This "series CTN" triac will commute the full RMS current at the maximum rated junction temperature ( $T_{j(max)} = 150\text{ °C}$ ) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

## 2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- High junction operating temperature capability ( $T_{j(max)} = 150\text{ °C}$ )
- High minimum IGT for guaranteed immunity to gate noise
- Full cycle AC conduction
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Protective self turn-on capability for high energy transients
- Safe clamping capability for low energy over-voltage transients
- Less sensitive gate for high noise immunity
- Triggering in three quadrants only
- Planar passivated for voltage ruggedness and reliability
- High commutation capability with maximum false trigger immunity
- Very high immunity to false turn-on by  $dV/dt$  and IEC 61000-4-4 fast transient
- Package is RoHS compliant
- Package meets UL94V0 flammability requirement

## 3. Applications

- Electronic thermostats (heating and cooling)
- High power motor controls e.g washing machine and vacuum cleaners
- Rectifier-fed DC inductive loads e.g DC motors and solenoids
- Refrigeration and air conditioning compressors
- Applications subject to high temperature ( $T_{j(max)} = 150\text{ °C}$ )

## 4. Quick reference data

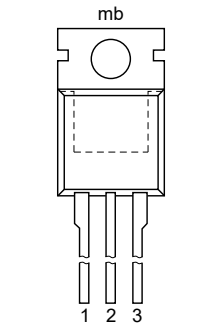
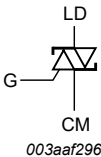
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 126\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	10	A

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>		-	-	90	A
		full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 16.7\text{ ms}$		-	-	99	A
$T_j$	junction temperature			-	-	150	$^{\circ}\text{C}$
$V_{PP}$	peak pulse voltage	$T_j = 25\text{ }^{\circ}\text{C}$ ; non-repetitive, off-state; <a href="#">Fig. 6</a>		-	-	2	kV
<b>Static characteristics</b>							
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD+ G+; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 8</a>		5	-	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD+ G-; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 8</a>		5	-	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD- G-; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 8</a>		5	-	35	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 10</a>		-	-	30	mA
$V_T$	on-state voltage	$I_T = 14\text{ A}$ ; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 11</a>		-	-	1.5	V
$V_{CL}$	clamping voltage	$I_{CL} = 0.1\text{ mA}$ ; $t_p = 1\text{ ms}$ ; $T_j = 25\text{ }^{\circ}\text{C}$		850	-	-	V
<b>Dynamic characteristics</b>							
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 125\text{ }^{\circ}\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit		4000	-	-	V/ $\mu\text{s}$
		$V_{DM} = 536\text{ V}$ ; $T_j = 150\text{ }^{\circ}\text{C}$ ; exponential waveform; gate open circuit		2000	-	-	V/ $\mu\text{s}$
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 150\text{ }^{\circ}\text{C}$ ; $I_{T(RMS)} = 10\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; gate open circuit; snubberless condition		5	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_j = 150\text{ }^{\circ}\text{C}$ ; $I_{T(RMS)} = 10\text{ A}$ ; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$ ; gate open circuit		10	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_j = 150\text{ }^{\circ}\text{C}$ ; $I_{T(RMS)} = 10\text{ A}$ ; $dV_{com}/dt = 1\text{ V}/\mu\text{s}$ ; gate open circuit		15	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	CM	common	 <p>TO-220AB (SOT78)</p>	 <p>003aaf296</p>
2	LD	load		
3	G	gate		
mb	LD	mounting base; load		

6. Ordering information

Table 3. Ordering information

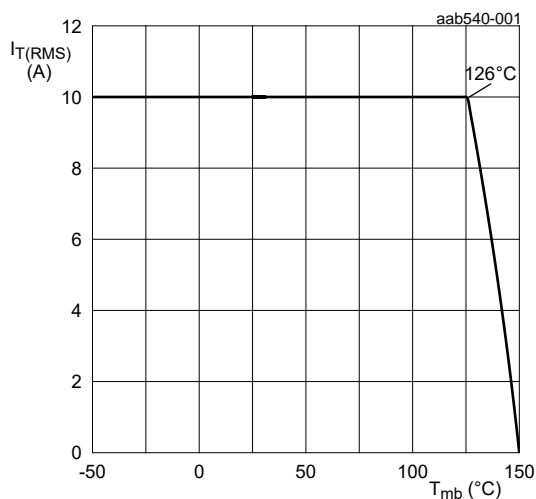
Type number	Package		
	Name	Description	Version
ACTT10-800CTN	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

## 7. Limiting values

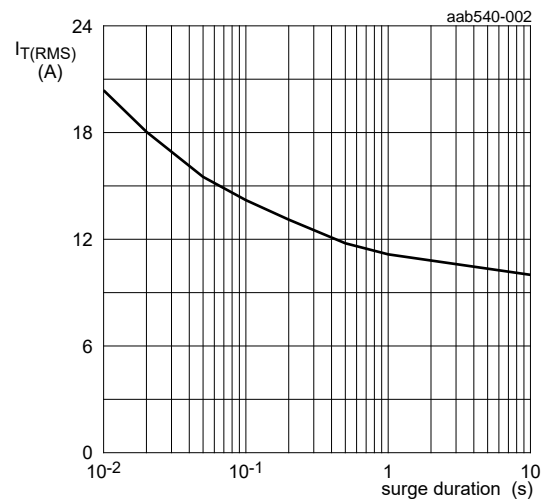
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{\text{DRM}}$	repetitive peak off-state voltage		-	800	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{mb}} \leq 126\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	10	A
$I_{\text{TSM}}$	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	90	A
		full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 16.7\text{ ms}$	-	99	A
$I^2t$	$I^2t$ for fusing	$t_{\text{p}} = 10\text{ ms}$ ; sine-wave pulse	-	40	$\text{A}^2\text{s}$
$di_{\text{T}}/dt$	rate of rise of on-state current	$I_{\text{G}} = 70\text{ mA}$	-	100	$\text{A}/\mu\text{s}$
$I_{\text{GM}}$	peak gate current	$t = 20\text{ }\mu\text{s}$	-	2	A
$P_{\text{GM}}$	peak gate power		-	5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	-	0.5	W
$T_{\text{stg}}$	storage temperature		-40	150	$^{\circ}\text{C}$
$T_{\text{j}}$	junction temperature		-	150	$^{\circ}\text{C}$
$V_{\text{PP}}$	peak pulse voltage	$T_{\text{j}} = 25\text{ }^{\circ}\text{C}$ ; non-repetitive, off-state; <a href="#">Fig. 6</a>	-	2	kV

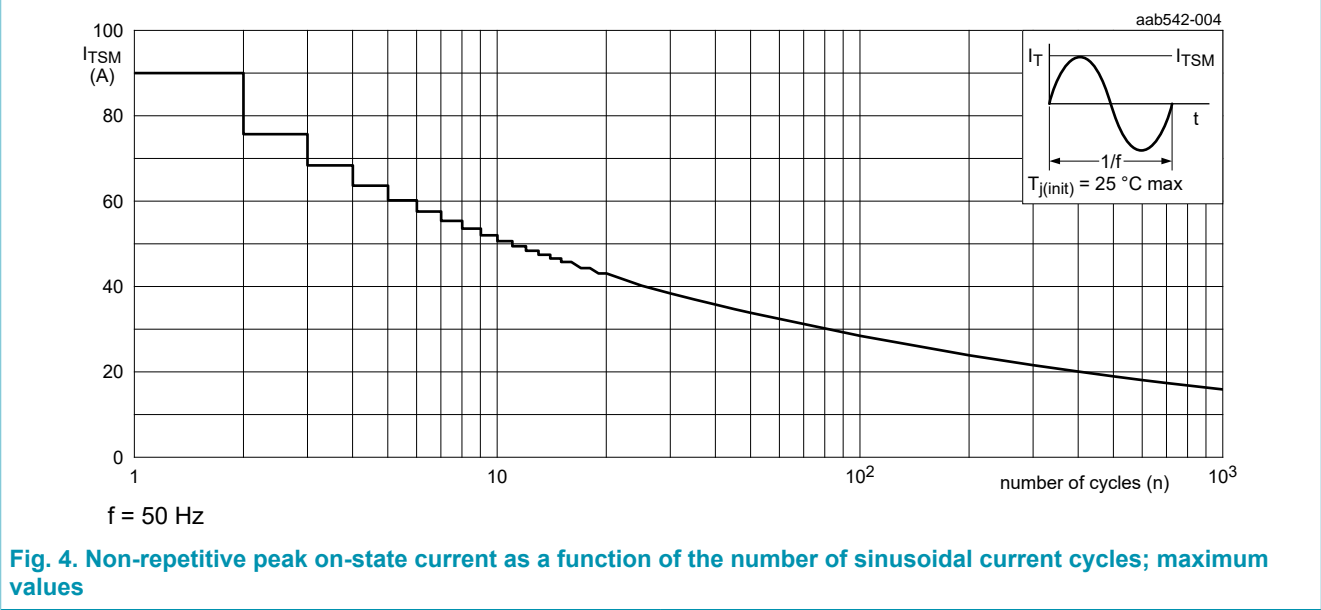
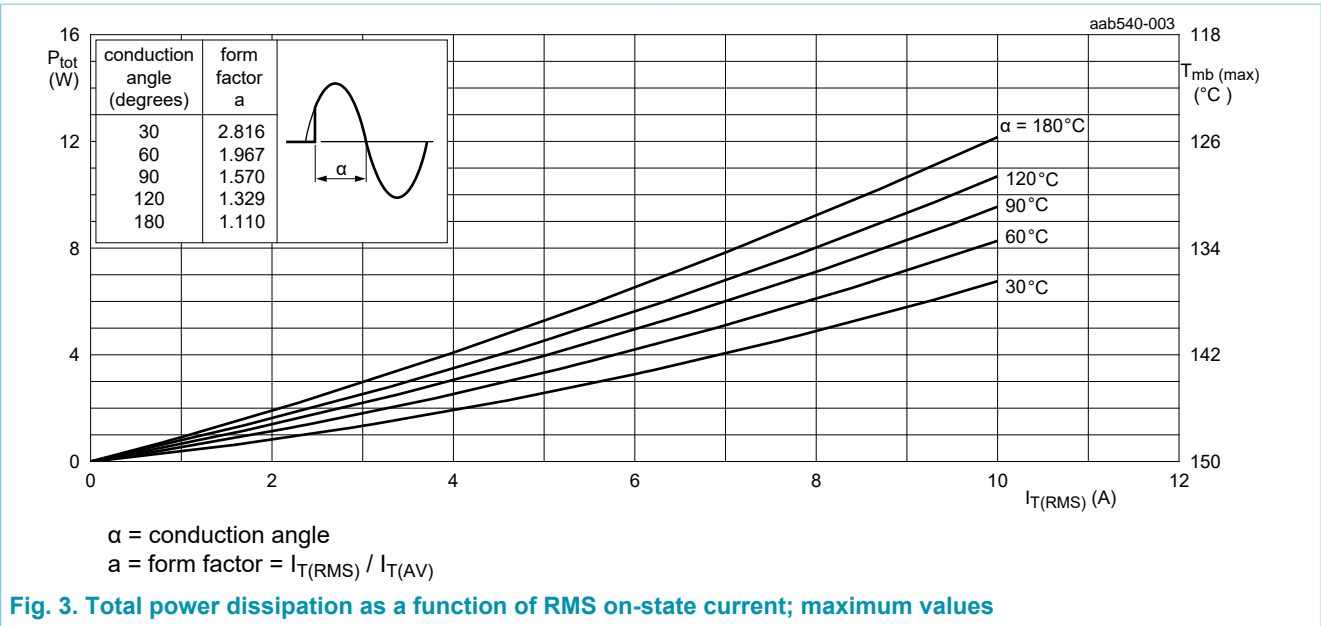


**Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values**



$f = 50\text{ Hz}$ ;  $T_{\text{mb}} = 126\text{ }^{\circ}\text{C}$

**Fig. 2. RMS on-state current as a function of surge duration; maximum values**



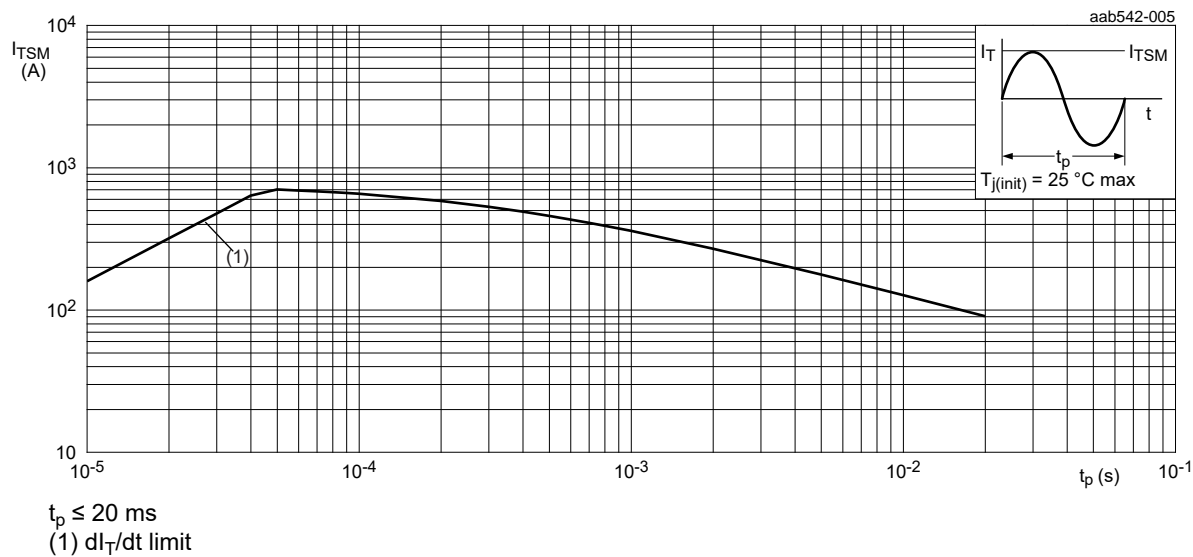


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

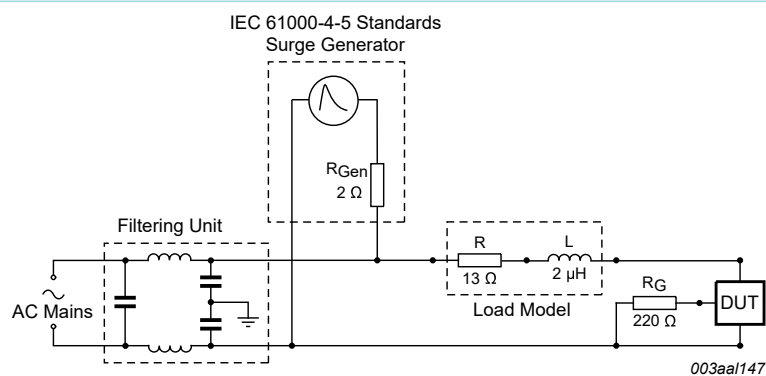


Fig. 6. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; <a href="#">Fig. 7</a>		-	-	2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W

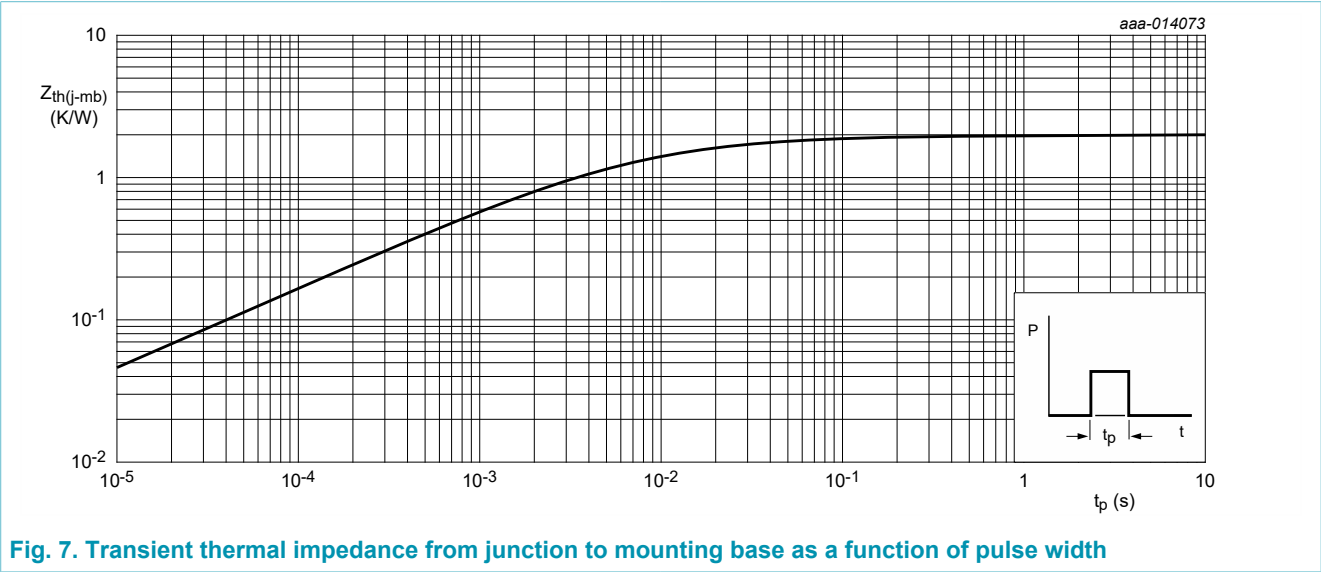


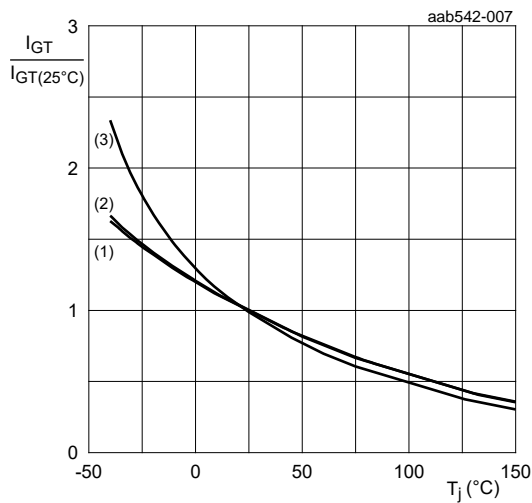
Fig. 7. Transient thermal impedance from junction to mounting base as a function of pulse width

## 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD+ G+; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>	5	-	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD+ G-; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>	5	-	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD- G-; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>	5	-	35	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 100\text{ mA}$ ; LD+ G+; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>	-	-	40	mA
		$V_D = 12\text{ V}$ ; $I_G = 100\text{ mA}$ ; LD+ G-; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>	-	-	50	mA
		$V_D = 12\text{ V}$ ; $I_G = 100\text{ mA}$ ; LD- G-; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>	-	-	40	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>	-	-	30	mA
$V_T$	on-state voltage	$I_T = 14\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>	-	-	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>	-	0.8	1	V
		$V_D = 400\text{ V}$ ; $I_T = 100\text{ mA}$ ; $T_j = 150\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>	0.2	0.5	-	V
$I_D$	off-state current	$V_D = 800\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$	-	-	10	$\mu\text{A}$
		$V_D = 800\text{ V}$ ; $T_j = 150\text{ }^\circ\text{C}$	-	-	2	mA
$V_{CL}$	clamping voltage	$I_{CL} = 0.1\text{ mA}$ ; $t_p = 1\text{ ms}$ ; $T_j = 25\text{ }^\circ\text{C}$	850	-	-	V
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	4000	-	-	V/ $\mu\text{s}$
		$V_{DM} = 536\text{ V}$ ; $T_j = 150\text{ }^\circ\text{C}$ ; exponential waveform; gate open circuit	2000	-	-	V/ $\mu\text{s}$
$di_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 150\text{ }^\circ\text{C}$ ; $I_{T(RMS)} = 10\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; gate open circuit; snubberless condition	5	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_j = 150\text{ }^\circ\text{C}$ ; $I_{T(RMS)} = 10\text{ A}$ ; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$ ; gate open circuit	10	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_j = 150\text{ }^\circ\text{C}$ ; $I_{T(RMS)} = 10\text{ A}$ ; $dV_{com}/dt = 1\text{ V}/\mu\text{s}$ ; gate open circuit	15	-	-	A/ms





- (1) LD+ G+
- (2) LD+ G-
- (3) LD- G-

Fig. 8. Normalized gate trigger current as a function of junction temperature

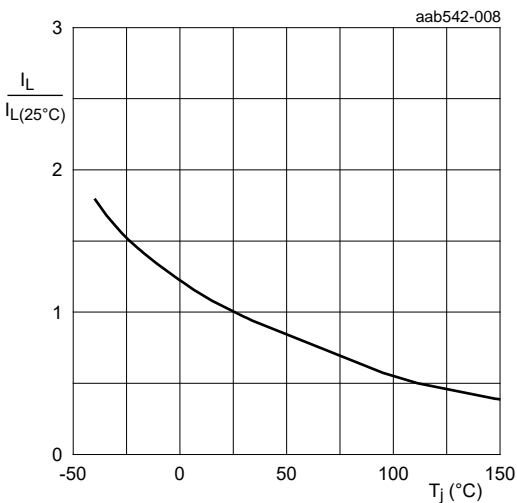


Fig. 9. Normalized latching current as a function of junction temperature

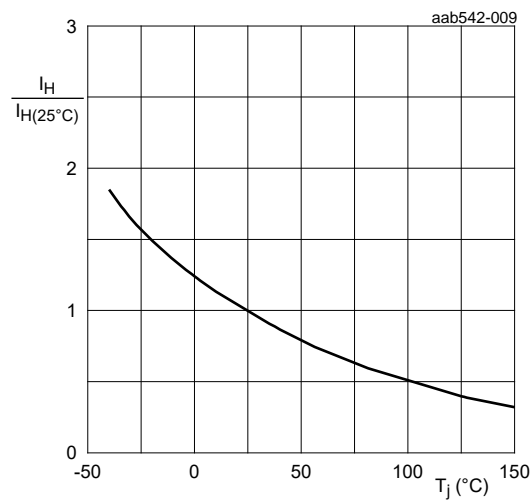
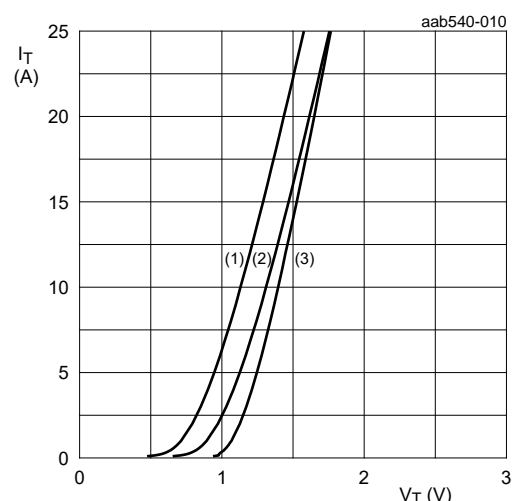


Fig. 10. Normalized holding current as a function of junction temperature



- $V_o = 0.984 \text{ V}$ ;  $R_s = 0.033 \Omega$
- (1)  $T_j = 150^{\circ}\text{C}$ ; typical values
  - (2)  $T_j = 150^{\circ}\text{C}$ ; maximum values
  - (3)  $T_j = 25^{\circ}\text{C}$ ; maximum values

Fig. 11. On-state current as a function of on-state voltage

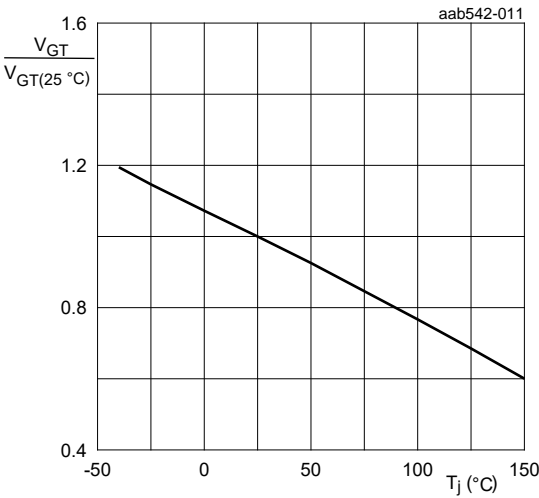
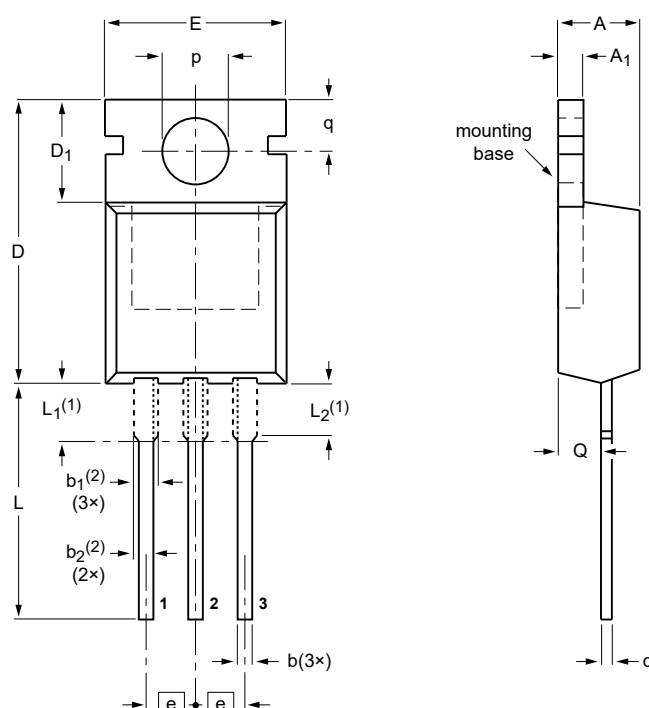


Fig. 12. Normalized gate trigger voltage as a function of junction temperature

## 10. Package outline

**Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB**

**SOT78**




**DIMENSIONS** (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub> (2)	b <sub>2</sub> (2)	c	D	D <sub>1</sub>	E	e	L	L <sub>1</sub> (1)	L <sub>2</sub> (1) max.	p	q	Q
mm	4.7	1.40	0.9	1.6	1.3	0.7	16.0	6.6	10.3	2.54	15.0	3.30	3.0	3.8	3.0	2.6
	4.1	1.25	0.6	1.0	1.0	0.4	15.2	5.9	9.7		12.8	2.79		3.5	2.7	2.2

## Notes

1. Lead shoulder designs may vary.
2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

**Fig. 13. Package outline TO-220AB (SOT78)**

## 11. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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Date of release: 28 March 2016

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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